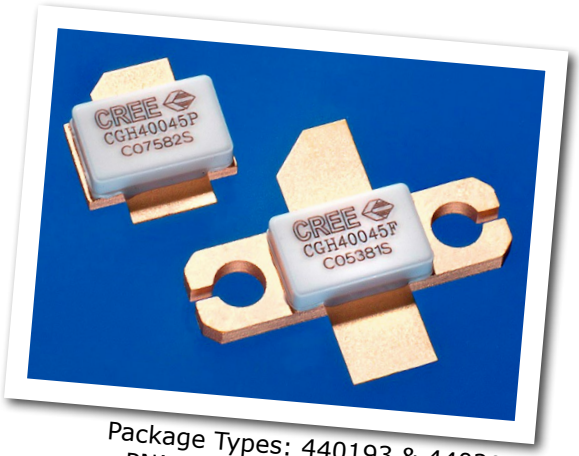
CGH40045

45 W, RF Power GaN HEMT

Cree's CGH40045 is an unmatched, gallium nitride (GaN) high electron mobility transistor (HEMT). The CGH40045, operating from a 28 volt rail, offers a general purpose, broadband solution to a variety of RF and microwave applications. GaN HEMTs offer high efficiency, high gain and wide bandwidth capabilities making the CGH40045 ideal for linear and compressed amplifier circuits. The transistor is available in a flange and pill package.



Package Types: 440193 & 440206
PN's: CGH40045F & CGH40045P

FEATURES

- Up to 4 GHz Operation
- 16 dB Small Signal Gain at 2.0 GHz
- 12 dB Small Signal Gain at 4.0 GHz
- 55 W Typical P_{SAT}
- 55 % Efficiency at P_{SAT}
- 28 V Operation

APPLICATIONS

- 2-Way Private Radio
- Broadband Amplifiers
- Cellular Infrastructure
- Test Instrumentation
- Class A, AB, Linear amplifiers suitable for OFDM, W-CDMA, EDGE, CDMA waveforms

Large Signal Models Available for SiC & GaN

Rev 3.5 – December 2012

Absolute Maximum Ratings (not simultaneous) at 25˚C Case Temperature

Parameter	Symbol	Rating	Units	Conditions
Drain-Source Voltage	V_{DSS}	84	Volts	25˚C
Gate-to-Source Voltage	V_{GS}	-10, +2	Volts	25˚C
Storage Temperature	T_{STG}	-65, +150	˚C	
Operating Junction Temperature	T_J	225	˚C	
Maximum Forward Gate Current	I_{GMAX}	15	mA	25˚C
Maximum Drain Current[1]	I_{DMAX}	6	A	25˚C
Soldering Temperature[2]	T_S	245	˚C	
Screw Torque	τ	80	in-oz	
Thermal Resistance, Junction to Case[3]	$R_{\theta JC}$	2.8	˚C/W	85˚C
Case Operating Temperature[3,4]	T_C	-40, +150	˚C	30 seconds

Note:
[1] Current limit for long term, reliable operation
[2] Refer to the Application Note on soldering at www.cree.com/products/wireless_appnotes.asp
[3] Measured for the CGH40045F at P_{DISS} = 56W.
[4] See also, the Power Dissipation De-rating Curve on Page 8.

Electrical Characteristics (T_C = 25˚C)

Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
DC Characteristics[1]						
Gate Threshold Voltage	$V_{GS(th)}$	-3.8	-3.0	-2.3	V_{DC}	V_{DS} = 10 V, I_D = 14.4 mA
Gate Quiescent Voltage	$V_{GS(Q)}$	–	-2.7	–	V_{DC}	V_{DS} = 28 V, I_D = 400 mA
Saturated Drain Current[2]	I_{DS}	11.6	14.0	–	A	V_{DS} = 6.0 V, V_{GS} = 2.0 V
Drain-Source Breakdown Voltage	V_{BR}	120	–	–	V_{DC}	V_{GS} = -8 V, I_D = 14.4 mA
RF Characteristics[3] (T_C = 25˚C, F_0 = 2.5 GHz unless otherwise noted)						
Small Signal Gain	G_{SS}	12.5	14	–	dB	V_{DD} = 28 V, I_{DQ} = 400 mA
Power Output[4]	P_{SAT}	40	55	–	W	V_{DD} = 28 V, I_{DQ} = 400 mA
Drain Efficiency[5]	η	45	55	–	%	V_{DD} = 28 V, I_{DQ} = 400 mA, P_{OUT} = P_{SAT}
Output Mismatch Stress	VSWR	–	–	10 : 1	Ψ	No damage at all phase angles, V_{DD} = 28 V, I_{DQ} = 400 mA, P_{OUT} = 45 W CW
Dynamic Characteristics						
Input Capacitance	C_{GS}	–	19.0	–	pF	V_{DS} = 28 V, V_{gs} = -8 V, f = 1 MHz
Output Capacitance	C_{DS}	–	5.9	–	pF	V_{DS} = 28 V, V_{gs} = -8 V, f = 1 MHz
Feedback Capacitance	C_{GD}	–	0.8	–	pF	V_{DS} = 28 V, V_{gs} = -8 V, f = 1 MHz

Notes:
[1] Measured on wafer prior to packaging.
[2] Scaled from PCM data.
[3] Measured in CGH40045F-TB.
[4] P_{SAT} is defined as I_G = 1.08 mA.
[5] Drain Efficiency = P_{OUT} / P_{DC}

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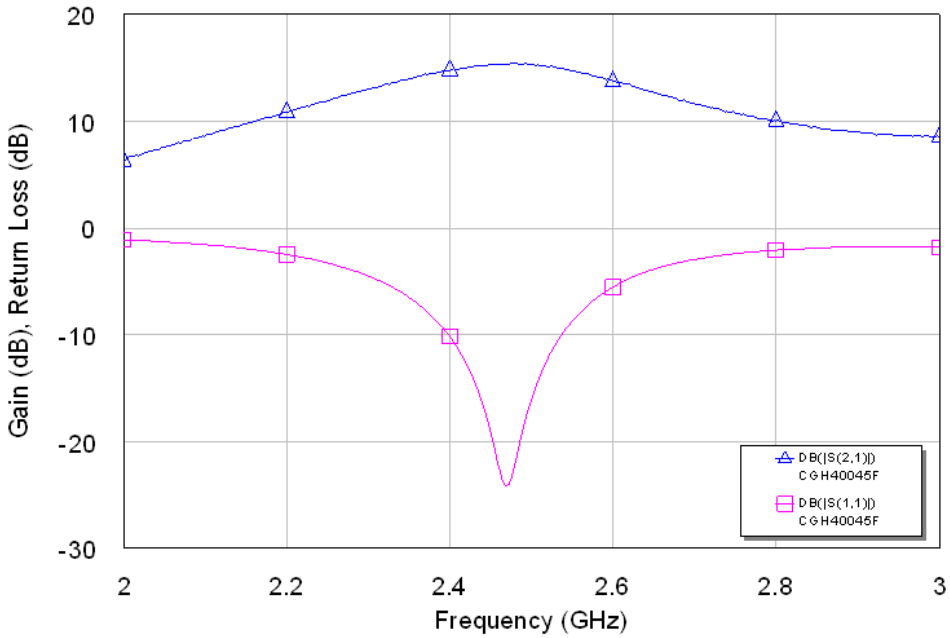
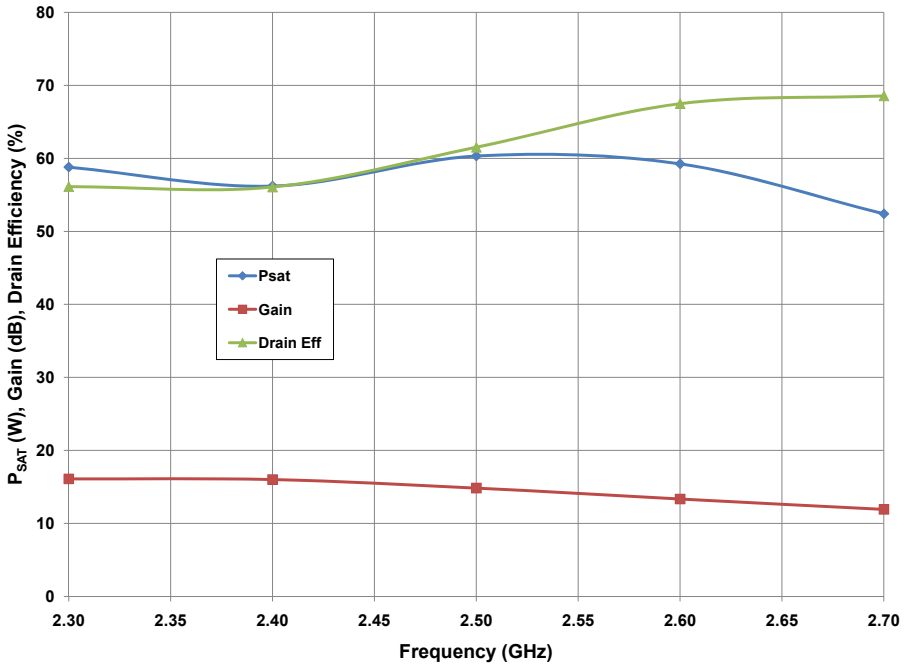
Typical Performance

Simulated Small Signal Gain and Input Return Loss of the CGH40045-TB vs Frequency
V_{DD} = 28 V, I_{DQ} = 400 mA



Gain, Efficiency, and Output Power vs Frequency of the CGH40045F measured in Amplifier Circuit CGH40045-TB
V_{DD} = 28 V, I_{DQ} = 400 mA



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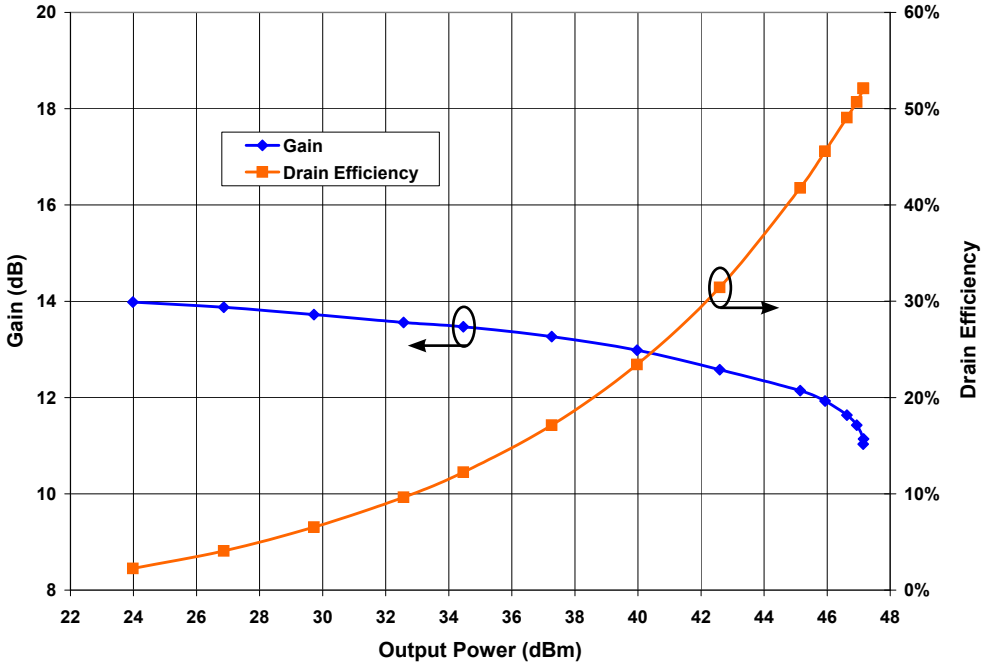
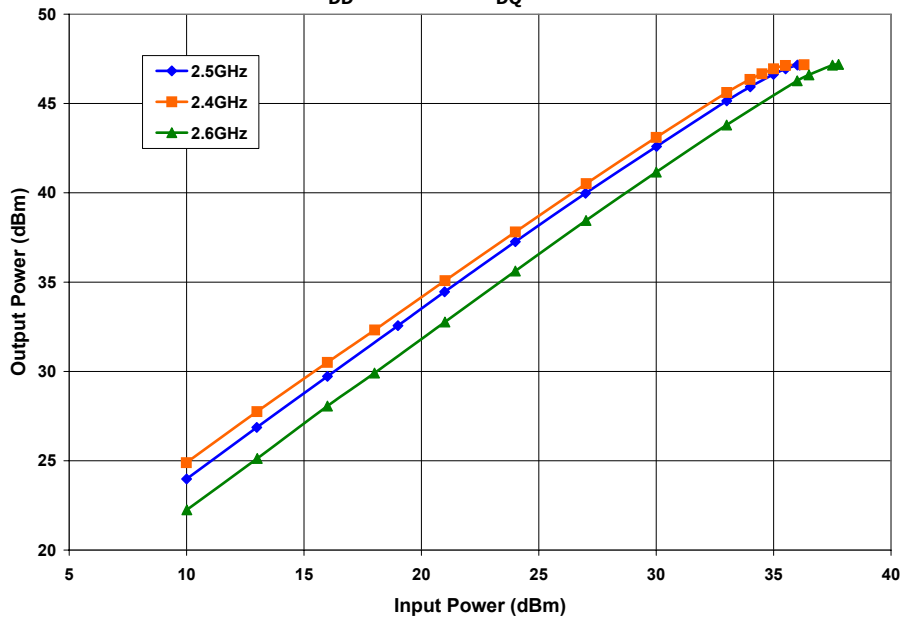
Typical Performance

Gain and Efficiency vs Output Power of the CGH40045 measured in Amplifier Circuit CGH40045F-TB
V_{DD} = 28 V, I_{DQ} = 400 mA, Freq = 2.5 GHz



Single Tone CW Output Power vs Input Power of the CGH40045 measured in Amplifier Circuit CGH40045F-TB
V_{DD} = 28 V, I_{DQ} = 400 mA



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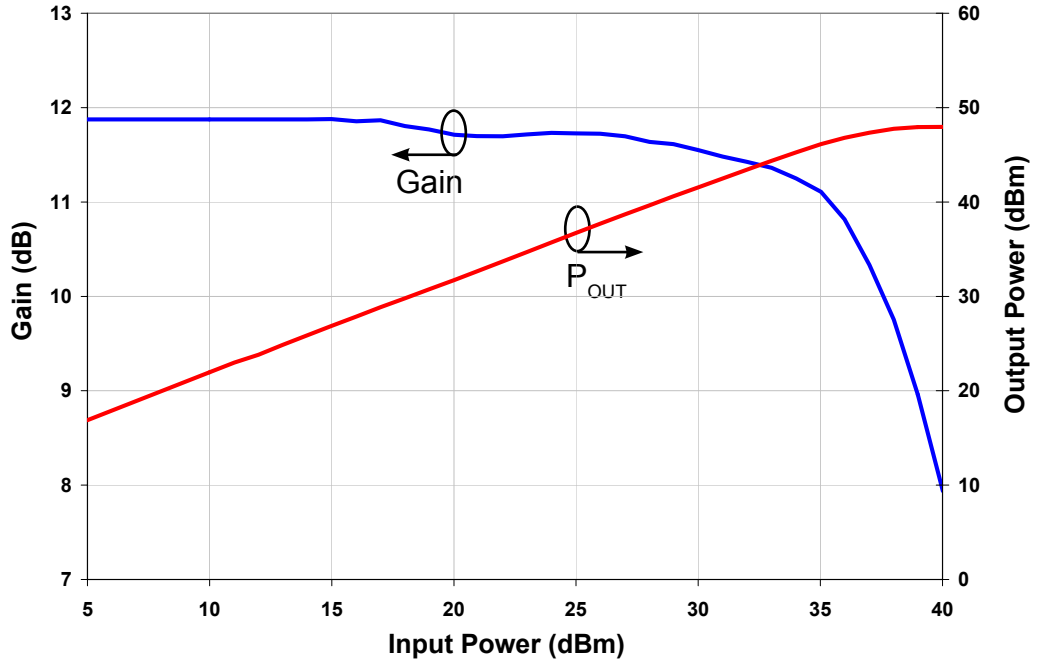
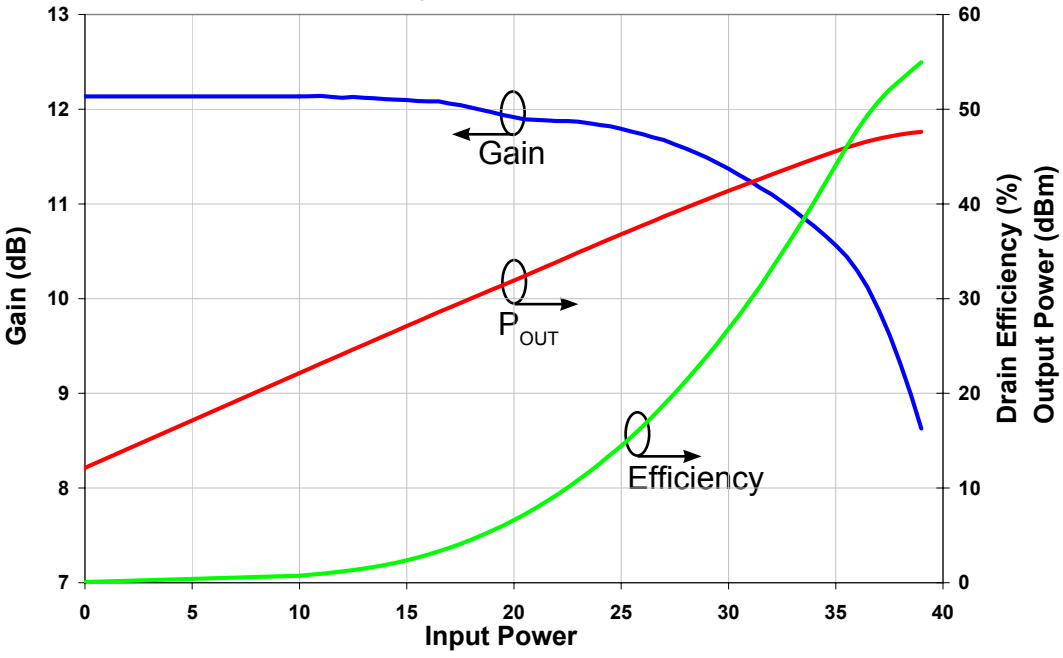
Typical Performance

Pulsed Gain and Output Power vs Input Power of the CGH40045 measured in an Amplifier Circuit
V_{DD} = 28 V, I_{DQ} = 800 mA, Freq = 3.6 GHz, Pulse Width=200µS, 10% Duty Cycle



Single Tone CW Gain, Efficiency, and Output Power vs Input Power of the CGH40045 measured in an Amplifier Circuit
V_{DD} = 28 V, I_{DQ} = 800 mA, Freq = 3.6 GHz



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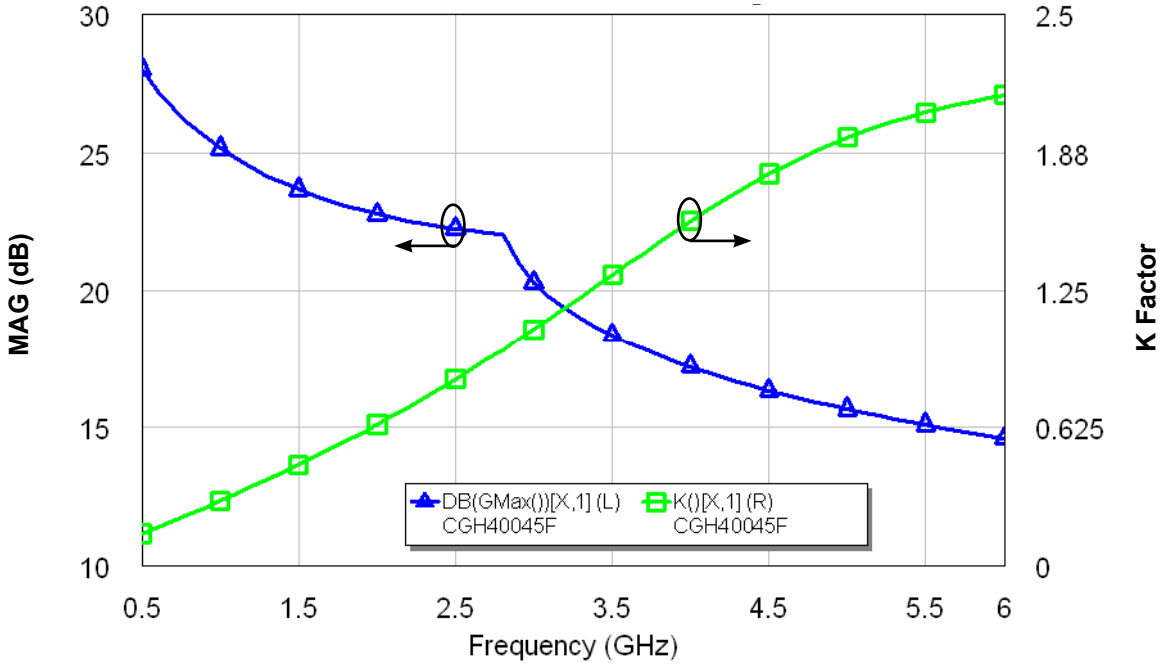
Typical Performance

Simulated Maximum Available Gain and K Factor of the CGH40045
V_{DD} = 28 V, I_{DQ} = 400 mA



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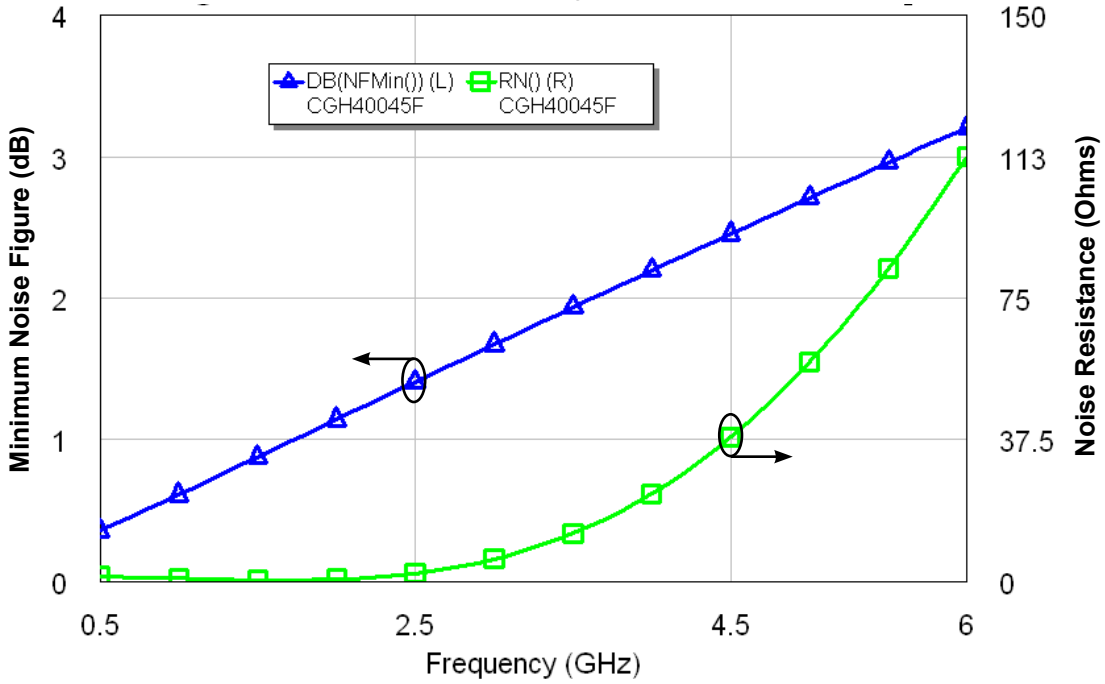
Typical Noise Performance

Simulated Minimum Noise Figure and Noise Resistance vs Frequency of the CGH40045
V_{DD} = 28 V, I_{DQ} = 400 mA



Electrostatic Discharge (ESD) Classifications

Parameter	Symbol	Class	Test Methodology
Human Body Model	HBM	1A > 250 V	JEDEC JESD22 A114-D
Charge Device Model	CDM	1 < 200 V	JEDEC JESD22 C101-C

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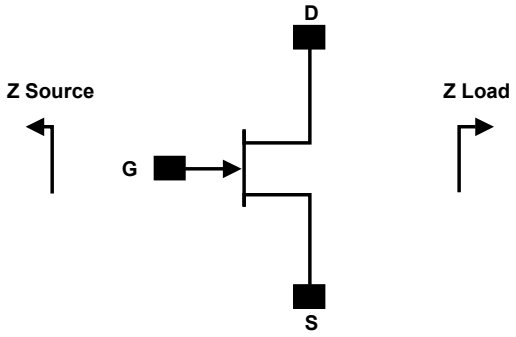
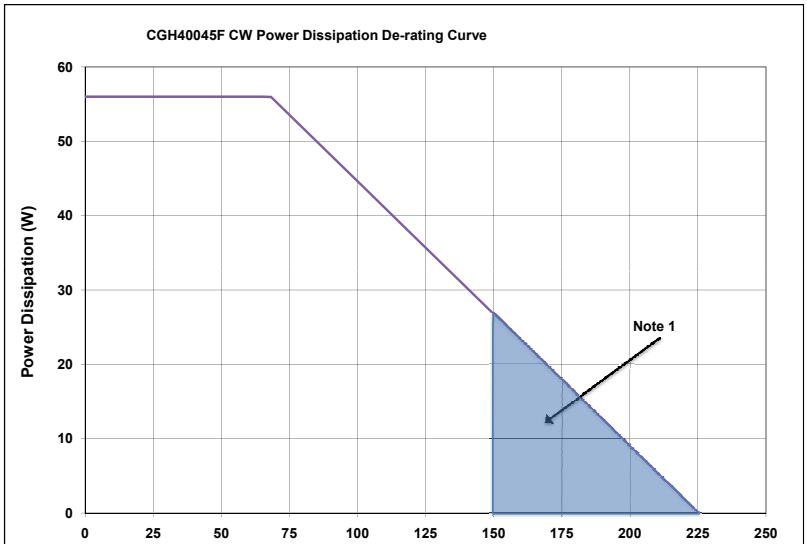
Simulated Source and Load Impedances



Frequency (MHz)	Z Source	Z Load
500	4.1 + j5.27	14.73 + j6.91
750	2.9 + j 4.1	12.3 + j 7.6
1000	2.48 + j0.06	8.13 + j6.85
1100	1.9 + j 3.1	9.2 + j 6.2
1500	2.1 - j 2.5	6.0 + j 4.3
1800	2.1 - j 1.9	5.8 + j 4.1
2000	0.69 - j3.75	4.93 + j0.16
2100	1.5 - j 4.4	5.1 + j 2.8
3000	1.06 - j8.92	4.04 - j2.98
4000	1.67 - j18.1	4.97 - j8.25

Note 1. V_{DD} = 28V, I_{DQ} = 800mA in the 440193 package.
Note 2. Optimized for power gain, P_{SAT} and PAE.
Note 3. When using this device at low frequency, series resistors should be used to maintain amplifier stability.

CGH40045 Power Dissipation De-rating Curve



Note 1. Area exceeds Maximum Case Operating Temperature (See Page 2).

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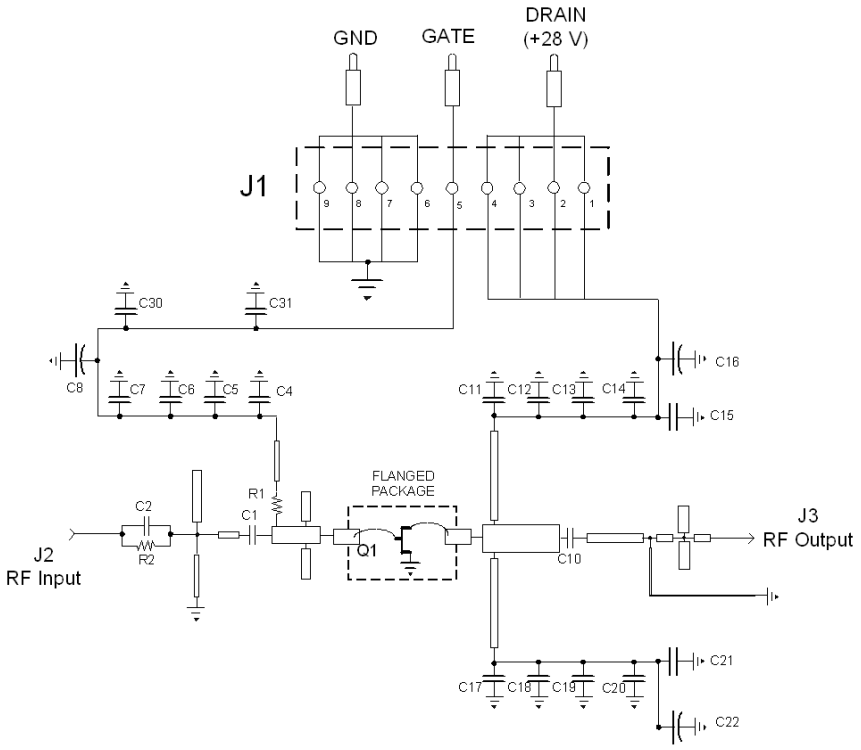
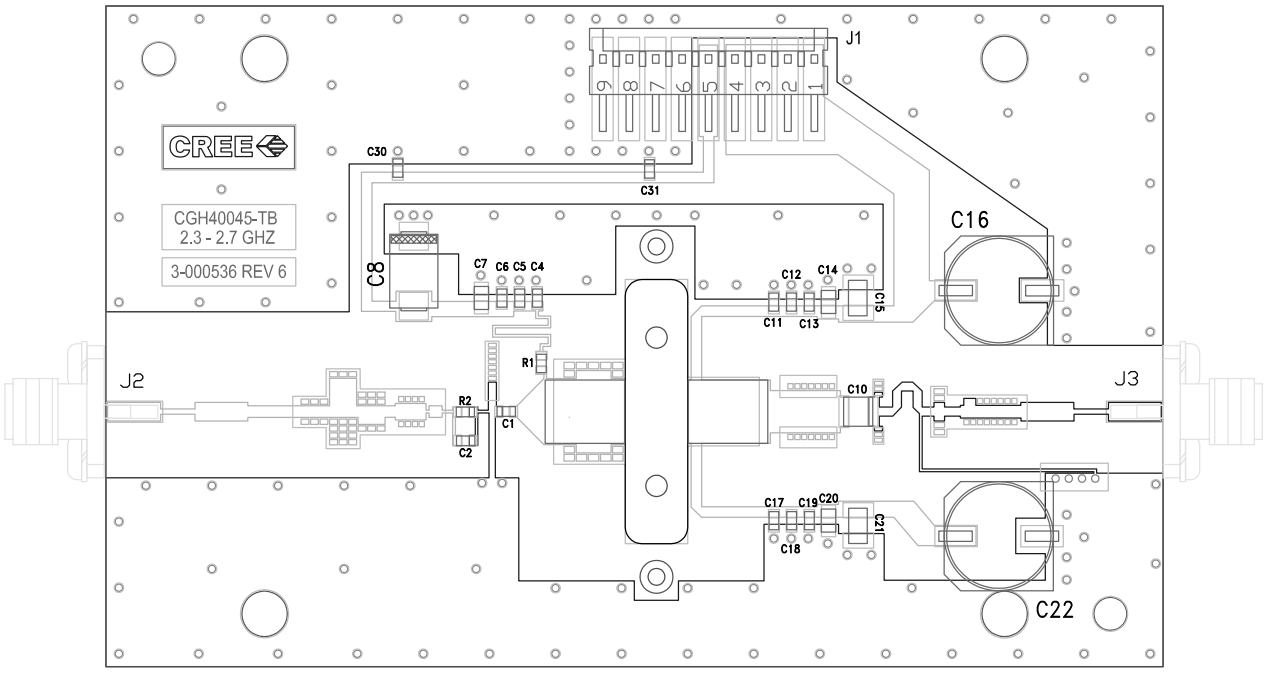
CGH40045-TB Demonstration Amplifier Circuit Schematic



CGH40045-TB Demonstration Amplifier Circuit Outline



Note: The device slot is machined to different depths to support either pill or flanged versions

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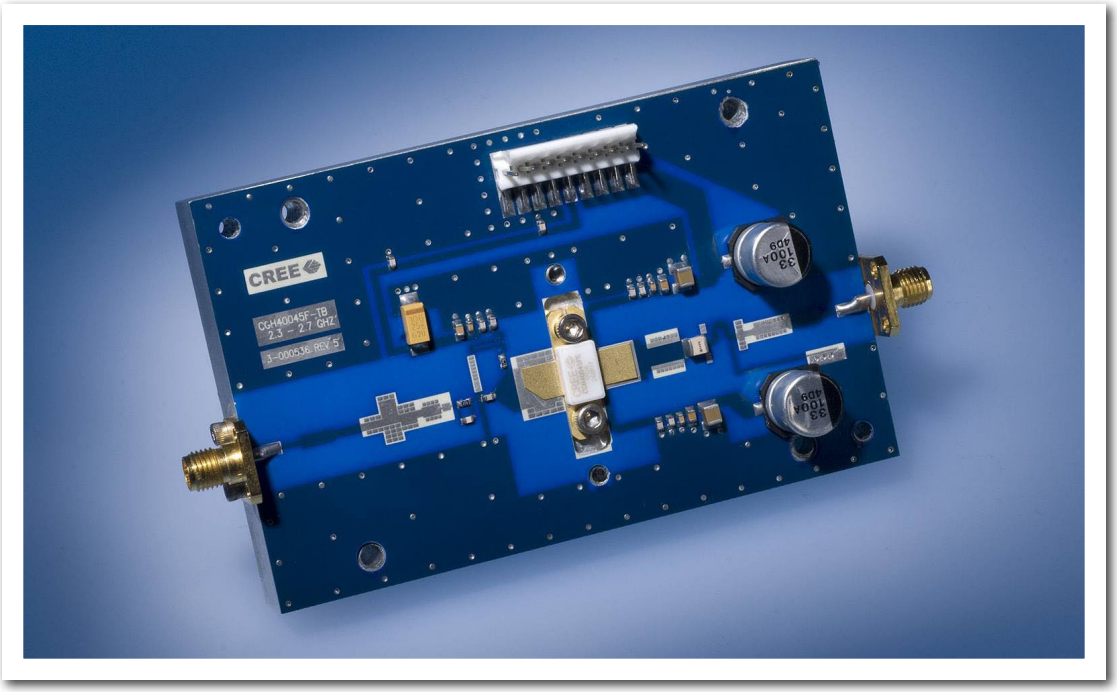
CGH40045-TB Demonstration Amplifier Circuit Bill of Materials

Designator	Description	Qty
C1	CAP, 0.8pF, ± 0.1 pF, 0603	1
C2	CAP, 2.2pF, ± 0.1 pF, 0603	1
C4,C11,C17	CAP, 10.0pF, +/-5%, 0603, ATC	3
C6,C13, C19	CAP, 470pF ±5 %, 100 V, 0603, X7R	3
C7,C14,C20	CAP,33000PF, 0805,100V, X7R	3
C8	CAP, 10UF, 16V, SMT, TANTALUM	1
C10	CAP, 8.2pF ±5%, ATC100B	1
C15,C21	CAP, 1.0UF ±10%, 100V, 1210, X7R	2
C5,C12,C18,C30,C31	CAP, 82.0pF, ±5%, 0603	5
C16,C22	CAP, 33UF, 20%, G CASE	2
R2	RES, 1/16W, 0603, 100 Ohms 1%	1
R1	RES, 1/16W, 0603, 5.1 Ohms 1%	1
J2,J3	CONN, SMA, PANEL MOUNT JACK, FLANGE	2
J1	CONN, HEADER, RT>PLZ .1CEN LK 9POS	1
-	PCB, RO4350B, Er = 3.48, h = 20 mil	1
Q1	CGH40045	1

CGH40045-TB Demonstration Amplifier Circuit



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Typical Package S-Parameters for CGH40045
(Small Signal, V_{DS} = 28 V, I_{DQ} = 400 mA, angle in degrees)

Frequency	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
500 MHz	0.941	-171.75	7.34	80.91	0.012	-3.58	0.650	-173.39
600 MHz	0.941	-174.07	6.12	77.22	0.012	-6.14	0.655	-173.73
700 MHz	0.941	-175.88	5.24	73.81	0.012	-8.41	0.660	-173.93
800 MHz	0.942	-177.39	4.59	70.58	0.012	-10.49	0.665	-174.05
900 MHz	0.942	-178.70	4.07	67.49	0.012	-12.42	0.671	-174.15
1.0 GHz	0.942	-179.88	3.66	64.51	0.011	-14.23	0.677	-174.24
1.1 GHz	0.943	179.05	3.33	61.61	0.011	-15.93	0.683	-174.35
1.2 GHz	0.943	178.03	3.05	58.78	0.011	-17.54	0.689	-174.49
1.3 GHz	0.944	177.07	2.82	56.03	0.011	-19.06	0.695	-174.66
1.4 GHz	0.944	176.13	2.62	53.33	0.011	-20.50	0.701	-174.86
1.5 GHz	0.945	175.21	2.45	50.69	0.011	-21.86	0.707	-175.10
1.6 GHz	0.945	174.30	2.30	48.10	0.011	-23.14	0.713	-175.37
1.7 GHz	0.945	173.40	2.17	45.56	0.011	-24.34	0.718	-175.68
1.8 GHz	0.946	172.49	2.06	43.05	0.010	-25.47	0.724	-176.02
1.9 GHz	0.946	171.58	1.96	40.59	0.010	-26.53	0.729	-176.40
2.0 GHz	0.946	170.65	1.87	38.16	0.010	-27.51	0.734	-176.81
2.1 GHz	0.946	169.70	1.80	35.76	0.010	-28.43	0.739	-177.25
2.2 GHz	0.946	168.73	1.73	33.39	0.010	-29.28	0.743	-177.72
2.3 GHz	0.946	167.73	1.67	31.03	0.010	-30.06	0.747	-178.21
2.4 GHz	0.945	166.70	1.62	28.70	0.010	-30.78	0.751	-178.74
2.5 GHz	0.945	165.63	1.57	26.37	0.010	-31.44	0.754	-179.28
2.6 GHz	0.945	164.53	1.54	24.06	0.010	-32.05	0.757	-179.85
2.7 GHz	0.944	163.38	1.50	21.74	0.009	-32.60	0.759	179.55
2.8 GHz	0.943	162.17	1.47	19.42	0.009	-33.10	0.761	178.93
2.9 GHz	0.942	160.91	1.45	17.09	0.009	-33.56	0.763	178.28
3.0 GHz	0.941	159.57	1.43	14.74	0.009	-33.99	0.764	177.61
3.2 GHz	0.938	156.68	1.41	9.95	0.009	-34.75	0.766	176.20
3.4 GHz	0.935	153.41	1.41	5.00	0.009	-35.46	0.765	174.68
3.6 GHz	0.930	149.66	1.42	-0.20	0.010	-36.21	0.763	173.05
3.8 GHz	0.923	145.28	1.46	-5.76	0.010	-37.13	0.758	171.27
4.0 GHz	0.914	140.09	1.52	-11.80	0.011	-38.39	0.751	169.35
4.2 GHz	0.903	133.82	1.60	-18.50	0.011	-40.21	0.742	167.23
4.4 GHz	0.888	126.08	1.71	-26.07	0.012	-42.86	0.729	164.90
4.6 GHz	0.868	116.32	1.86	-34.83	0.013	-46.72	0.712	162.27
4.8 GHz	0.842	103.74	2.05	-45.14	0.015	-52.24	0.690	159.29
5.0 GHz	0.811	87.25	2.27	-57.50	0.017	-59.93	0.663	155.80
5.2 GHz	0.777	65.61	2.51	-72.38	0.019	-70.34	0.628	151.60
5.4 GHz	0.752	38.13	2.72	-90.03	0.021	-83.73	0.581	146.39
5.6 GHz	0.753	6.31	2.83	-110.07	0.023	-99.76	0.516	139.81
5.8 GHz	0.785	-25.54	2.78	-131.39	0.023	-117.31	0.427	131.59
6.0 GHz	0.835	-53.19	2.58	-152.64	0.022	-135.03	0.311	121.26

Download this s-parameter file in ".s2p" format at http://www.cree.com/products/wireless_s-parameters.asp

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(Small Signal, V_{DS} = 28 V, I_{DQ} = 800 mA, angle in degrees)

Frequency	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
500 MHz	0.952	-172.90	7.23	81.83	0.009	-1.13	0.688	-176.19
600 MHz	0.952	-175.11	6.03	78.47	0.009	-3.05	0.691	-176.58
700 MHz	0.952	-176.85	5.18	75.35	0.009	-4.72	0.694	-176.86
800 MHz	0.952	-178.32	4.54	72.38	0.009	-6.21	0.696	-177.07
900 MHz	0.952	-179.59	4.05	69.53	0.009	-7.58	0.699	-177.25
1.0 GHz	0.952	179.25	3.65	66.76	0.009	-8.84	0.702	-177.42
1.1 GHz	0.952	178.19	3.33	64.06	0.009	-10.01	0.706	-177.59
1.2 GHz	0.952	177.18	3.06	61.42	0.009	-11.09	0.709	-177.77
1.3 GHz	0.952	176.22	2.83	58.82	0.009	-12.11	0.712	-177.96
1.4 GHz	0.952	175.28	2.64	56.27	0.009	-13.05	0.716	-178.17
1.5 GHz	0.952	174.37	2.48	53.75	0.009	-13.92	0.719	-178.41
1.6 GHz	0.952	173.46	2.34	51.27	0.009	-14.72	0.722	-178.67
1.7 GHz	0.952	172.55	2.21	48.82	0.009	-15.46	0.725	-178.95
1.8 GHz	0.952	171.64	2.11	46.39	0.009	-16.14	0.728	-179.26
1.9 GHz	0.952	170.72	2.01	43.99	0.009	-16.75	0.731	-179.59
2.0 GHz	0.951	169.78	1.93	41.60	0.009	-17.29	0.734	-179.94
2.1 GHz	0.951	168.83	1.86	39.23	0.009	-17.78	0.737	179.67
2.2 GHz	0.951	167.85	1.80	36.88	0.008	-18.21	0.739	179.27
2.3 GHz	0.950	166.84	1.74	34.53	0.008	-18.58	0.741	178.83
2.4 GHz	0.949	165.80	1.69	32.19	0.008	-18.90	0.743	178.38
2.5 GHz	0.949	164.73	1.65	29.85	0.008	-19.17	0.744	177.90
2.6 GHz	0.948	163.61	1.61	27.51	0.008	-19.40	0.746	177.39
2.7 GHz	0.947	162.44	1.58	25.15	0.008	-19.59	0.747	176.86
2.8 GHz	0.946	161.22	1.56	22.79	0.008	-19.74	0.747	176.31
2.9 GHz	0.945	159.94	1.54	20.40	0.009	-19.87	0.748	175.73
3.0 GHz	0.943	158.58	1.53	17.98	0.009	-19.99	0.747	175.12
3.2 GHz	0.940	155.64	1.51	13.04	0.009	-20.21	0.746	173.83
3.4 GHz	0.935	152.30	1.51	7.90	0.009	-20.51	0.743	172.44
3.6 GHz	0.930	148.47	1.54	2.47	0.010	-21.01	0.738	170.92
3.8 GHz	0.922	143.99	1.58	-3.34	0.010	-21.86	0.730	169.27
4.0 GHz	0.913	138.66	1.65	-9.68	0.011	-23.25	0.721	167.47
4.2 GHz	0.900	132.21	1.75	-16.72	0.012	-25.41	0.708	165.49
4.4 GHz	0.884	124.23	1.87	-24.68	0.013	-28.63	0.691	163.32
4.6 GHz	0.863	114.16	2.04	-33.86	0.015	-33.25	0.671	160.90
4.8 GHz	0.835	101.18	2.24	-44.66	0.017	-39.70	0.646	158.17
5.0 GHz	0.802	84.20	2.47	-57.54	0.020	-48.45	0.616	155.00
5.2 GHz	0.768	62.03	2.72	-72.91	0.022	-59.96	0.577	151.18
5.4 GHz	0.745	34.19	2.91	-90.96	0.025	-74.38	0.527	146.39
5.6 GHz	0.750	2.50	2.99	-111.20	0.026	-91.25	0.459	140.32
5.8 GHz	0.785	-28.66	2.91	-132.50	0.027	-109.41	0.366	132.93
6.0 GHz	0.837	-55.46	2.67	-153.57	0.025	-127.56	0.245	124.60

Download this s-parameter file in ".s2p" format at http://www.cree.com/products/wireless_s-parameters.asp

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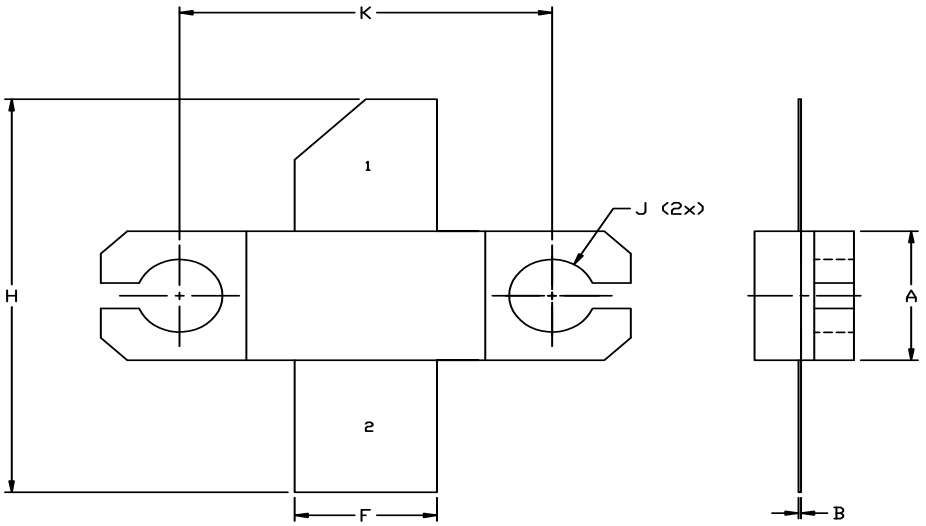
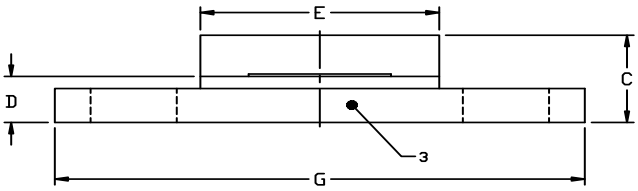
Product Dimensions CGH40045F (Package Type — 440193)





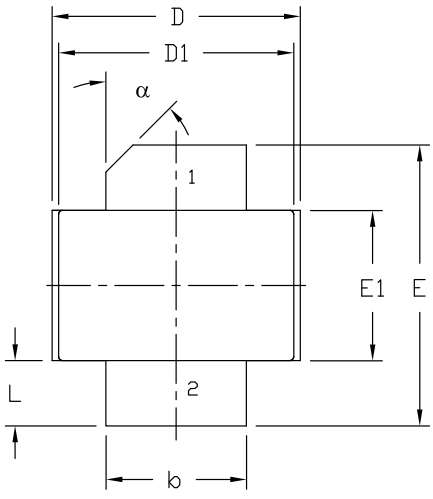
NOTES:

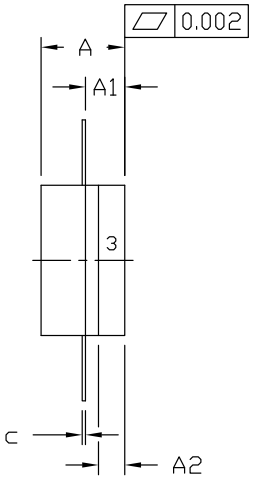
1. DIMENSIONING AND TOLERANICING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF 0.020" BEYOND EDGE OF LID.
4. LID MAY BE MISALIGNED TO THE BODY OF THE PACKAGE BY A MAXIMUM OF 0.008" IN ANY DIRECTION.
5. ALL PLATED SURFACES ARE NI/AU

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.225	0.235	5.72	5.97
B	0.004	0.006	0.10	0.15
C	0.145	0.165	3.18	4.19
D	0.077	0.087	1.96	2.21
E	0.355	0.365	9.02	9.27
F	0.210	0.220	5.33	5.59
G	0.795	0.805	20.19	20.45
H	0.670	0.730	17.02	18.54
J	ø .130		3.30	
k	0.562		14.28	

PIN 1. GATE
PIN 2. DRAIN
PIN 3. SOURCE

Product Dimensions CGH40045P (Package Type — 440206)





NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M – 1994.
2. CONTROLLING DIMENSION: INCH.
3. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF 0.020" BEYOND EDGE OF LID.
4. LID MAY BE MISALIGNED TO THE BODY OF PACKAGE BY A MAXIMUM OF 0.008" IN ANY DIRECTION.

DIM	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	0.125	0.145	3.18	3.68	
A1	0.057	0.067	1.45	1.70	
A2	0.035	0.045	0.89	1.14	
b	0.210	0.220	5.33	5.59	2x
c	0.004	0.006	0.10	0.15	2x
D	0.375	0.385	9.53	9.78	
D1	0.355	0.365	9.02	9.27	
E	0.400	0.460	10.16	11.68	
E1	0.225	0.235	5.72	5.97	
L	0.085	0.115	2.16	2.92	2x
α	45° REF		45° REF		

PIN 1. GATE
2. DRAIN
3. SOURCE

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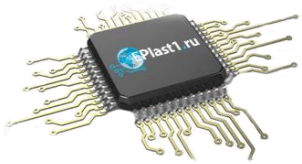
Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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